

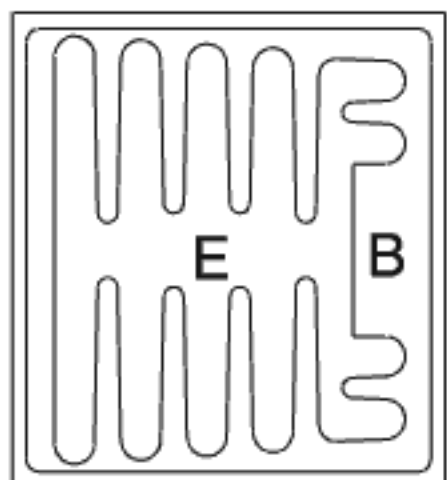
**PROCESS CP576**  
**Power Transistor**  
PNP - Amp/Switch Transistor Chip

**Central**<sup>TM</sup>  
Semiconductor Corp.

**PROCESS DETAILS**

Process	MULTI EPITAXIAL PLANAR
Die Size	203 x 227 MILS
Die Thickness	12.5 ± 1.0 MILS
Base Bonding Pad Area	38 x 76 MILS
Emitter Bonding Pad Area	47 x 72 MILS
Top Side Metalization	Al - 50,000Å
Back Side Metalization	Ag - 10,000Å

**GEOMETRY**



BACKSIDE COLLECTOR R0

**GROSS DIE PER 4 INCH WAFER**

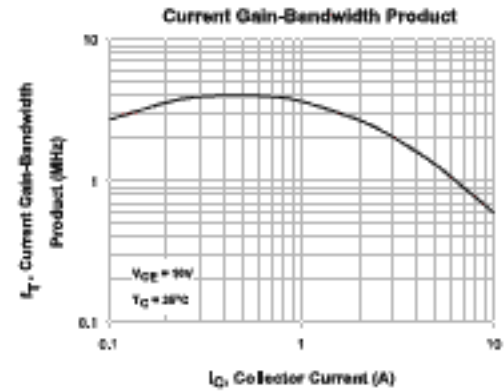
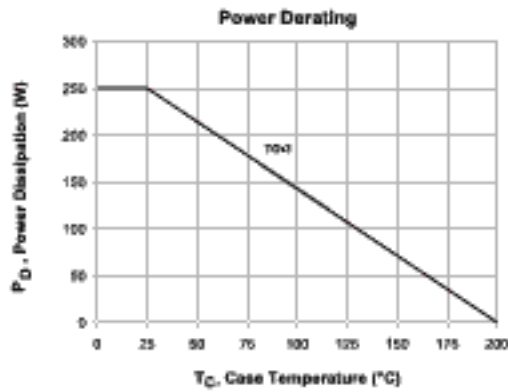
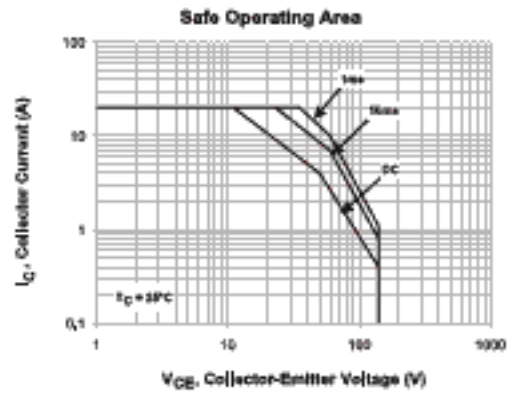
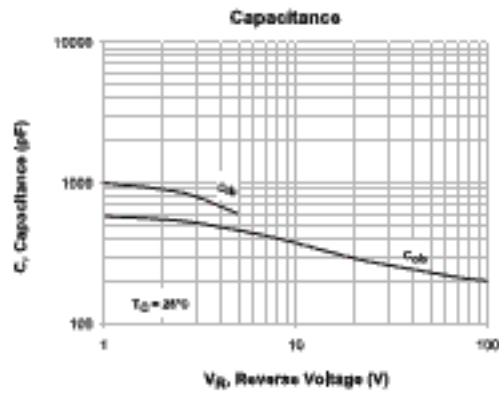
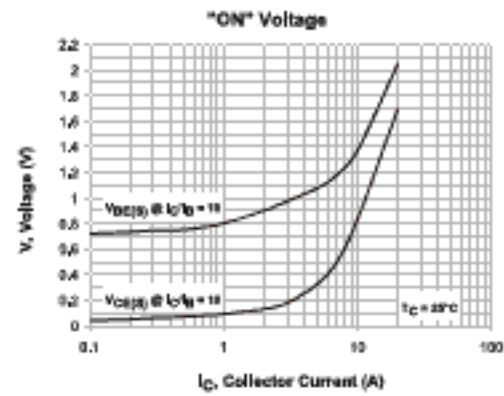
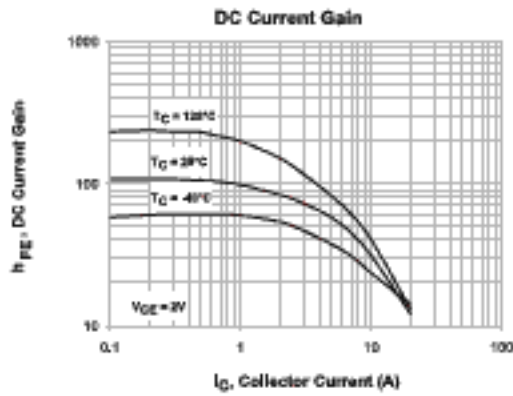
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**PRINCIPAL DEVICE TYPES**

MJ15004

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R2 (1-August 2002)



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